IN THE CLAIMS:

1.-34. (Cancelled)

35. (New) A semiconductor light emitting device comprising:

a base substrate;

a multilayer epitaxial structure includes a first conductive layer, a second conductive layer and a light emitting layer that is formed between the first conductive layer and the second conductive layer, the multilayer epitaxial structure being formed on the base substrate in such a manner that the first conductive layer is positioned closer to the base substrate than the second conductive layer is;

a first electrode that is formed on the first conductive layer;

a second electrode that is formed on the second conductive layer;

a first power supply terminal and a second power supply terminal that are formed on a main surface of the base substrate which faces away from the multilayer epitaxial structure;

a first conductive member including a first through hole that is provided in the base substrate, and electrically connecting the first electrode and the first power supply terminal;

a second conductive member including a second through hole that is provided in the base substrate, and electrically connecting the second electrode and the second power supply terminal; and

a phosphor film that covers a main surface of the multilayer epitaxial structure which faces away from the base substrate, and every side surface of the multilayer epitaxial structure from a layer including the main surface to include at least the light emitting layer.

36. (New) The semiconductor light emitting device of Claim 35, wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

37. (New) The semiconductor light emitting device of Claim 35, further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

38. (New) The semiconductor light emitting device of Claim 35, wherein

the first conductive layer is a p-type semiconductor layer, and

the second conductive layer is an n-type semiconductor layer.

39. (New) The semiconductor light emitting device of Claim 38, wherein

a main surface of the n-type semiconductor layer which faces away from the light emitting layer is uneven so as to improve light extraction efficiency.

40. (New) The semiconductor light emitting device of Claim 35 wherein

the multilayer epitaxial structure is formed through epitaxial growth, on a single-crystal substrate different from the base substrate, and transferred from the single-crystal substrate to the base substrate.

41. (New) The semiconductor light emitting device of Claim 40, wherein

the multilayer epitaxial structure is transferred to the base substrate in such a manner that a last epitaxially-grown layer having grown on the single-crystal substrate is positioned closer to the base substrate than a first epitaxially-grown layer is.

42. (New) The semiconductor light emitting device of Claim 35 wherein the base substrate is a SiC substrate.

43. (New) The semiconductor light emitting device of Claim 35 wherein the epitaxial structure has an uneven p-electrode surface as a second conductive layer.

44. (New) The semiconductor light emitting device of Claim 43 wherein a plurality of depressions is formed on a surface of the p-electrode surface to improve light extraction efficiency.

45. (New) The semiconductor light emitting device of Claim 43 wherein a Ni/An thin film and an ITO transparent electrode form the p-electrode.